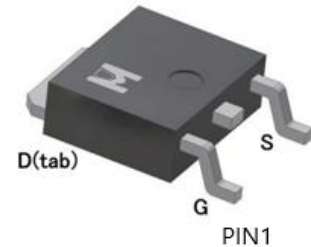
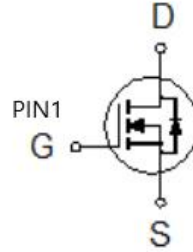


N-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

	N-CH
BV_{DSS}	30V
$R_{DS(on)} (MAX.) @ V_{GS}=10V$	9.0m Ω
$R_{DS(on)} (MAX.) @ V_{GS}=4.5V$	13.5m Ω
$I_D @ T_C=25^{\circ}C$	58A



Single N Channel MOSFET

UIS, Rg 100% Tested

Pb-Free Lead Plating & Halogen Free

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^{\circ}C$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C = 25^{\circ}C$	I_D	58	A
	$T_C = 100^{\circ}C$		36	
Pulsed Drain Current ¹		I_{DM}	140	
Avalanche Current		I_{AS}	31	
Avalanche Energy	$L = 0.1mH$	E_{AS}	48	mJ
Repetitive Avalanche Energy ²	$L = 0.05mH$	E_{AR}	24	
Power Dissipation	$T_C = 25^{\circ}C$	P_D	50	W
	$T_C = 100^{\circ}C$		20	
Operating Junction & Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^{\circ}C$

100% UIS testing in condition of $V_D=25V$, $L=0.1mH$, $V_G=10V$, $I_L=20A$, Rated $V_{DS}=25V$ N-CH

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	$R_{\theta JC}$		2.5	$^{\circ}C / W$
Junction-to-Ambient	$R_{\theta JA}$		75	

¹Pulse width limited by maximum junction temperature.

²Duty cycle $\leq 1\%$

³75 $^{\circ}C / W$ when mounted on a 1 in² pad of 2 oz copper.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	1.7	3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24V, V_{GS} = 0V$			1	μA
		$V_{DS} = 20V, V_{GS} = 0V, T_J = 125\text{ }^{\circ}C$			25	
On-State Drain Current ¹	$I_{D(ON)}$	$V_{DS} = 10V, V_{GS} = 10V$	58			A
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 25A$		7.5	9	m Ω
		$V_{GS} = 4.5V, I_D = 15A$		11	13.5	
Forward Transconductance ¹	g_{fs}	$V_{DS} = 5V, I_D = 20A$		20		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 15V, f = 1MHz$		905		pF
Output Capacitance	C_{oss}			135		
Reverse Transfer Capacitance	C_{rss}			82		
Gate Resistance	R_g	$V_{GS} = 15mV, V_{DS} = 0V, f = 1MHz$		3.4		Ω
Total Gate Charge ^{1,2}	$Q_g(V_{GS}=10V)$	$V_{DS} = 15V, V_{GS} = 10V,$ $I_D = 25A$		16.7		nC
	$Q_g(V_{GS}=4.5V)$			8.4		
Gate-Source Charge ^{1,2}	Q_{gs}			2.3		
Gate-Drain Charge ^{1,2}	Q_{gd}			3.5		
Turn-On Delay Time ^{1,2}	$t_{d(on)}$	$V_{DS} = 15V,$ $I_D = 1A, V_{GS} = 10V, R_{GS} = 6\Omega$		8		nS
Rise Time ^{1,2}	t_r			15		
Turn-Off Delay Time ^{1,2}	$t_{d(off)}$			20		
Fall Time ^{1,2}	t_f			20		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T _C = 25 °C)						
Continuous Current	I_S				58	A
Pulsed Current ³	I_{SM}				140	
Forward Voltage ¹	V_{SD}	$I_F = I_S, V_{GS} = 0V$			1.3	V
Reverse Recovery Time	t_{rr}	$I_F = I_S, dI_F/dt = 100A / \mu S$		22		nS
Peak Reverse Recovery Current	$I_{RM(REC)}$			180		A
Reverse Recovery Charge	Q_{rr}			12		nC

¹Pulse test : Pulse Width $\leq 300 \mu\text{sec}$, Duty Cycle $\leq 2\%$.

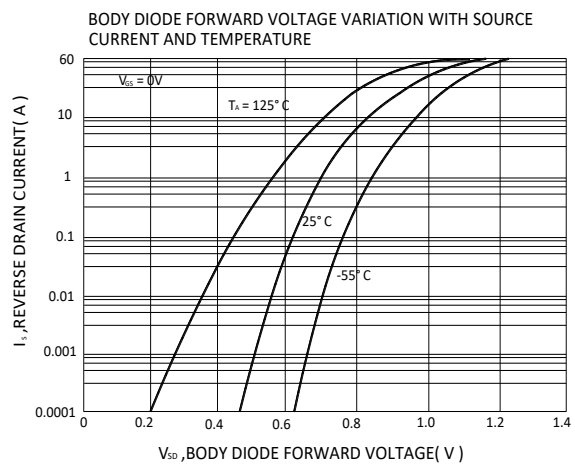
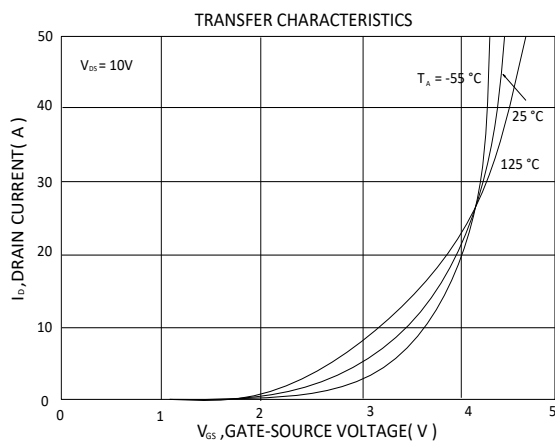
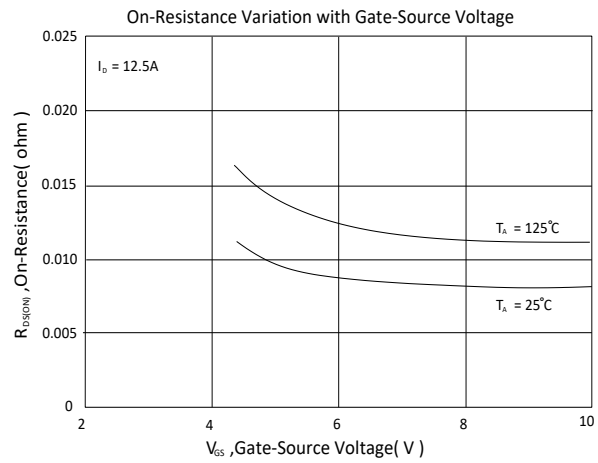
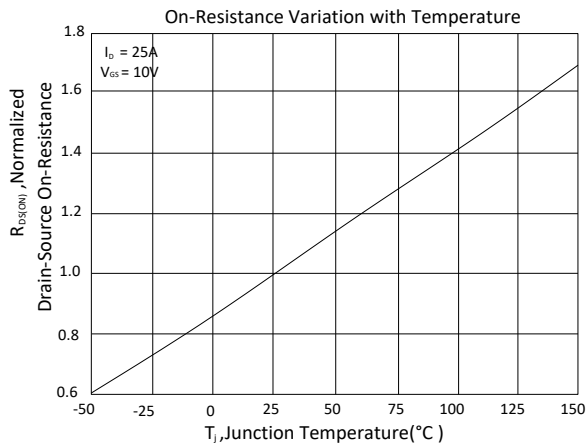
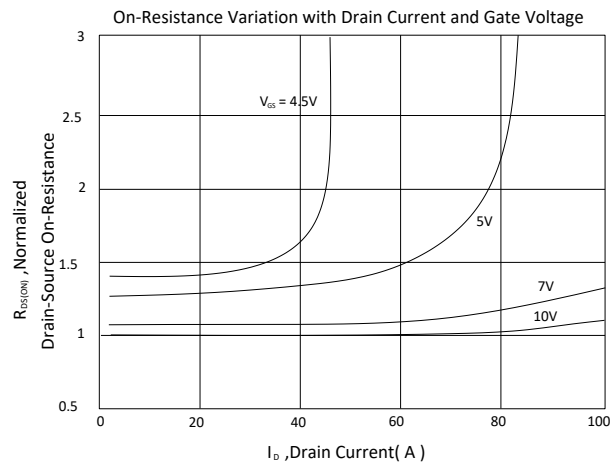
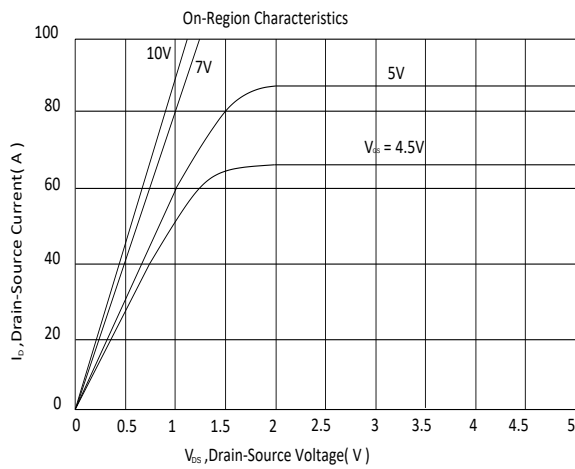
²Independent of operating temperature.

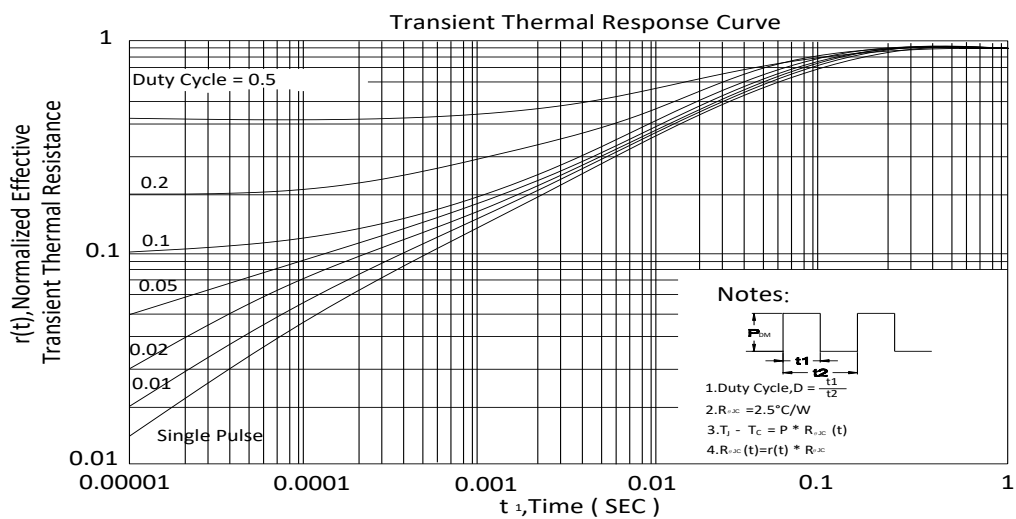
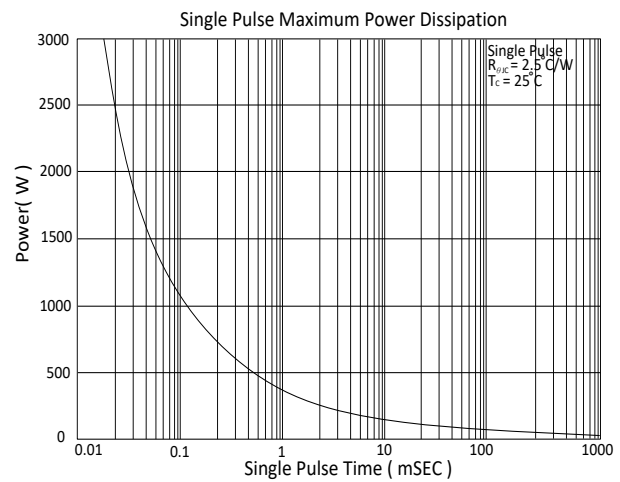
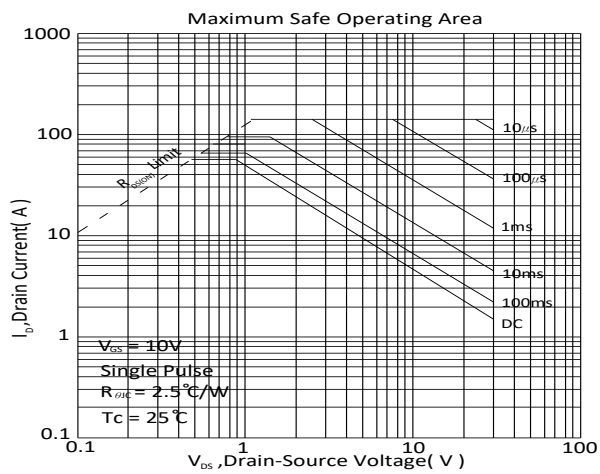
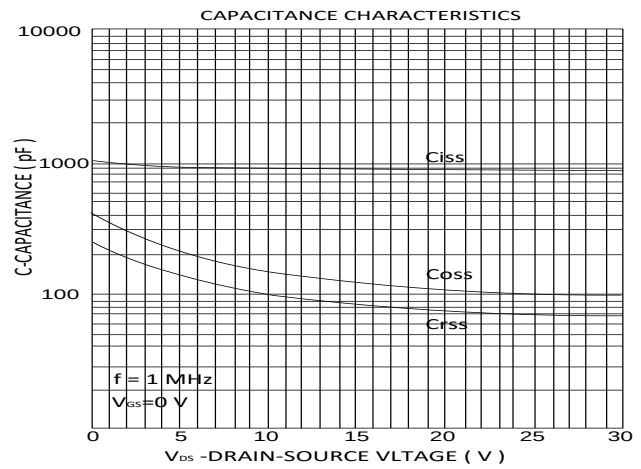
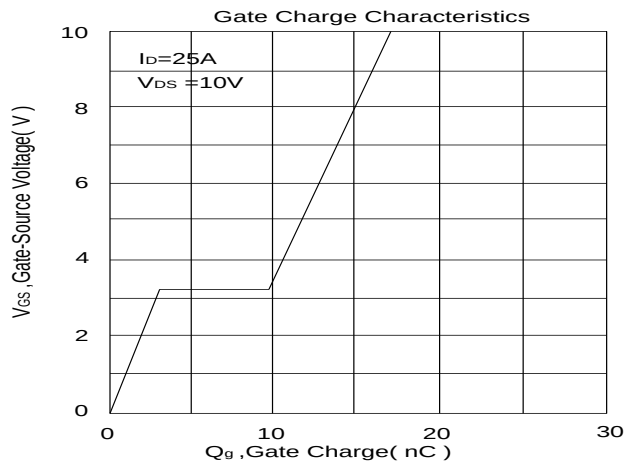
³Pulse width limited by maximum junction temperature.

EMC will review datasheet by quarter, and update new version.



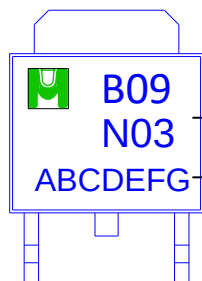
TYPICAL CHARACTERISTICS





Ordering & Marking Information:

Device Name: EMB09N03A for DPAK (TO252-2)



B09N03: Device Name

ABCDEFGH: Date Code

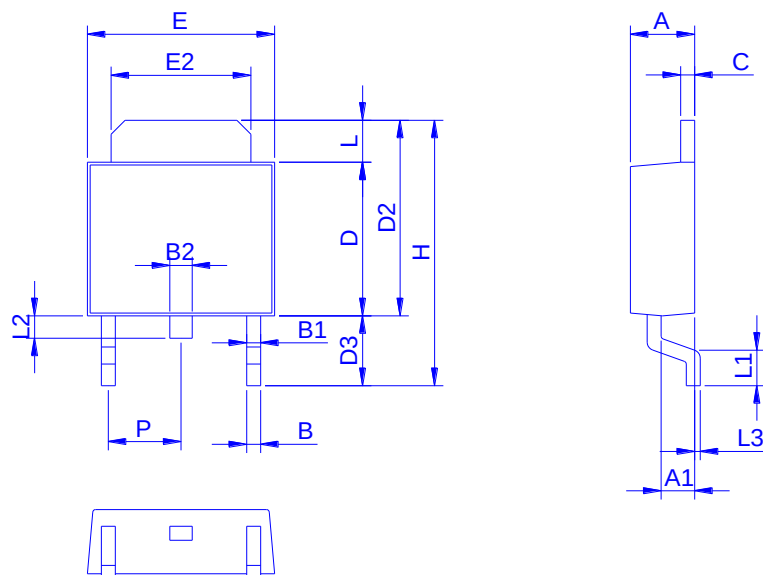
A: Assembly House

B: Year(A:2008 B:2009 C:2010....)

C: Month(A:01 B:02 C:03 D:04 E:05 F:06 G:07 H:08 I:09 J:10 K:11 L:12)

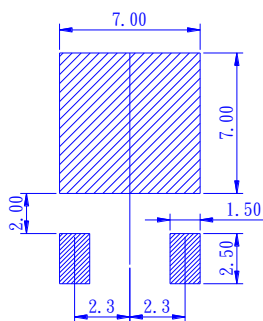
DEFG: Serial No.

Outline Drawing

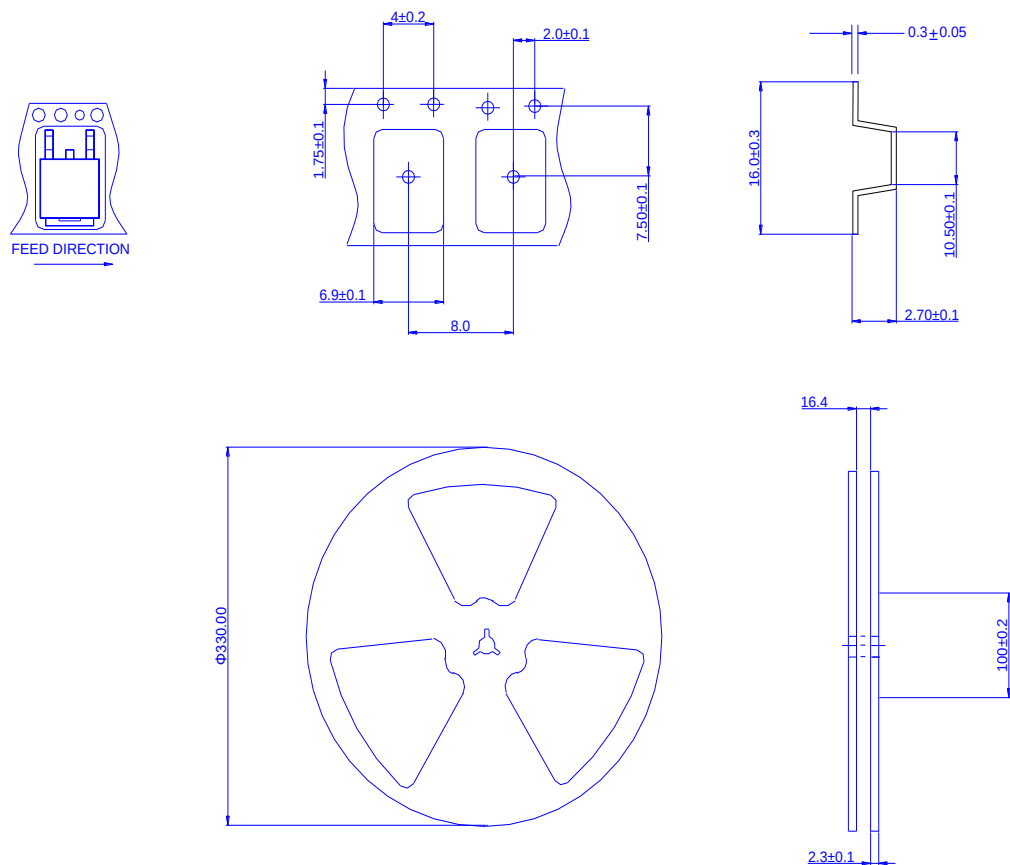


Dimension	A	A1	B	B1	B2	C	D	D2	D3	E	E2	H	L	L1	L2	L3	P
Min.	2.10	0.95	0.30	0.40	0.60	0.40	5.30	6.70	2.20	6.40	4.80	9.20	0.89	0.90	0.50	0.00	2.10
Max.	2.50	1.30	0.85	0.94	1.00	0.60	6.20	7.30	3.00	6.70	5.45	10.15	1.70	1.65	1.10	0.30	2.50

Footprint



◆ Tape&Reel Information:2500pcs/Reel(Dimension in millimeter)



產品別	TO252-2
Reel 尺寸	13"
編帶方式	FEED DIRECTION 
前空格	35
後空格	35
裝箱數	
滿捲數量	2.5K
捲/內盒比	1 : 1
內盒滿箱數	2.5K
內/外箱比	10 : 1